





Phase Control Thyristor

Preliminary Information

DS6140-2 October 2014 (LN32030)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Bridge Rectifiers
- High Voltage Power Supplies
- Motor Drives

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR3640H85* DCR3640H80 DCR3640H75	8500 8000 7500	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 600\text{mA}, \\ V_{DRM}, V_{RRM} t_p &= 10\text{ms}, \\ V_{DSM} \& V_{RSM} &= \\ V_{DRM} \& V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. *8200V @ -40° C, 8500V @ 0° C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR3640H85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

8500V
3640A
54000A
2000V/μs
200A/μs

* Higher dV/dt selections available

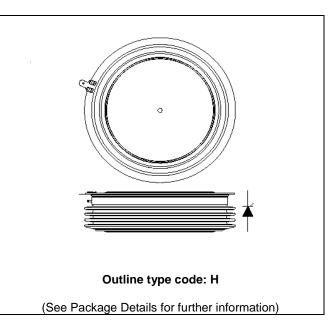


Fig. 1 Package outline





CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	3640	А
I _{T(RMS)}	RMS value	-	5718	А
I _T	Continuous (direct) on-state current	-	5306	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125$ °C	54.0	kA
l ² t	I ² t for fusing	$V_R = 0$	14.58	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.004255	°C/W
		Single side cooled	Anode DC	-	0.008	°C/W
			Cathode DC	-	0.0093	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 135.0kN	Double side	-	0.0009	°C/W
		(with mounting compound)	Single side	-	0.0018	°C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			120	155	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	600	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	500	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
V _{T(TO)}	Threshold voltage – Low level	500 to 4000A at T _{case} = 125°	С	-	1.21	V
	Threshold voltage – High level	4000 to 8000A at T _{case} = 125	°C	-	1.4067	V
r _T	On-state slope resistance – Low level	500A to 4000A at T _{case} = 125°C		-	0.33	mΩ
	On-state slope resistance – High level	4000A to 8000A at T _{case} = 125°C		-	0.2767	mΩ
t _{gd}	Delay time	V_D = 67% V_{DRM} , gate source 30V, 10Ω		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$I_T = 3000A$, $T_j = 125$ °C, $V_R = 200V$, $dI/dt = 1A/\mu s$,			1000	μs
		dV _{DR} /dt = 20V/μs linear				
Qs	Stored charge	- I _T = 3000A, T _j = 125°C, dl/dt – 1A/μs, V _{Rpeak} ~5100V, V _R ~ 3400V		3400	6700	μC
I _{RR}	Reverse recovery current			46	63	А
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
IH	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_T = 5A$		-	300	mA





GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Parameter Test Conditions		Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

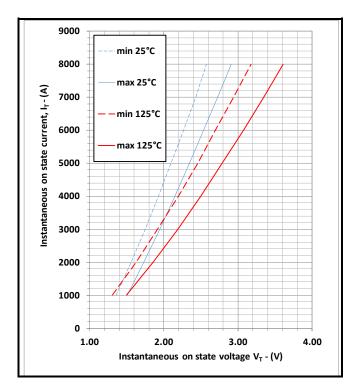


Fig.2 Maximum & minimum on-state characteristics

 V_{TM} EQUATION Where

A = 2.035252B = -0.20854

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ C = 0.000150

D = 0.02514

these values are valid for $T_j = 125$ °C for $I_T 500$ A to 8000A



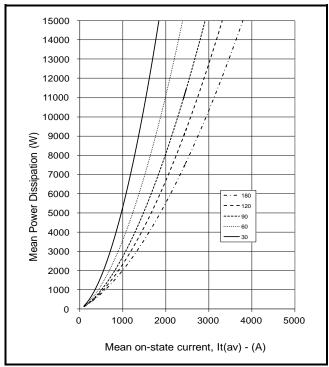


Fig.3 On-state power dissipation - sine wave

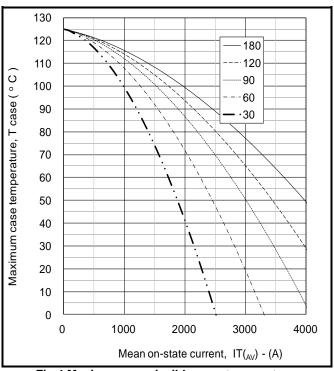


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

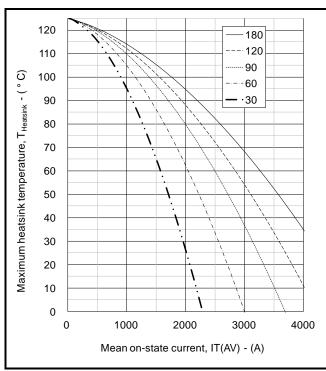


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

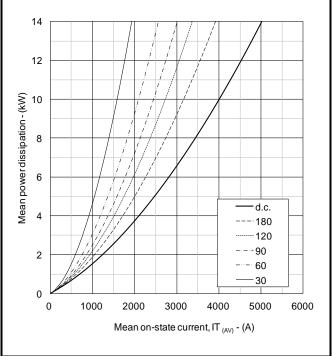


Fig.6 On-state power dissipation - rectangular wave



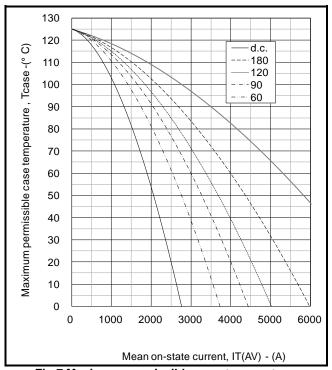


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

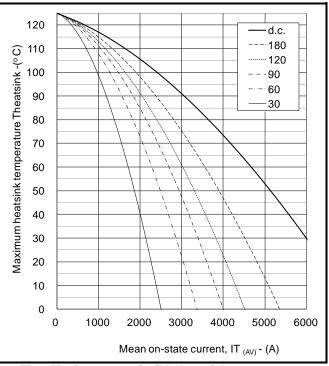


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave

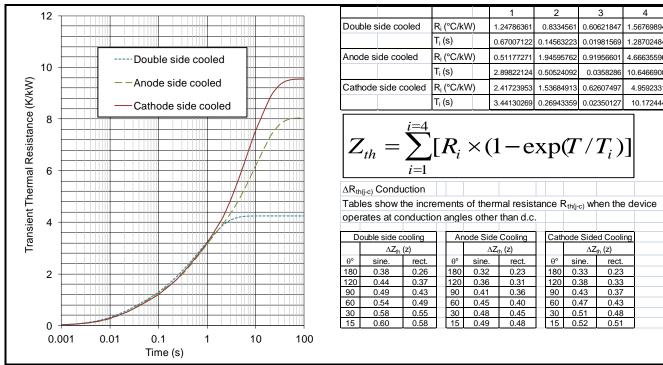
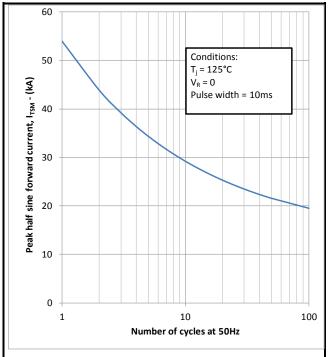
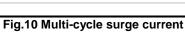


Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)







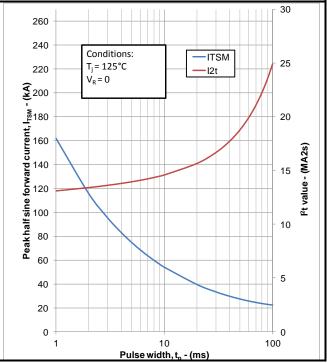


Fig.11 Single-cycle surge current

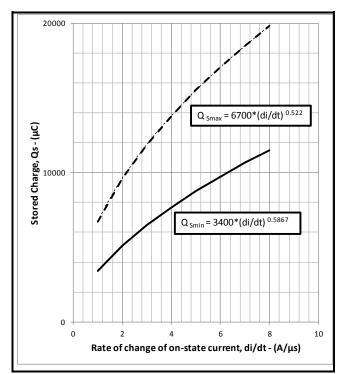


Fig.12 Stored charge

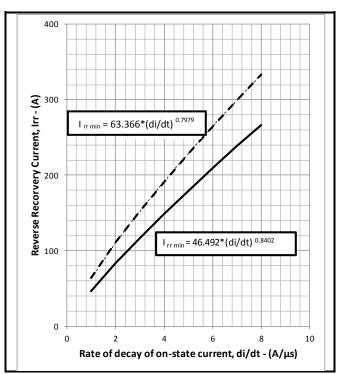


Fig.13 Reverse recovery current

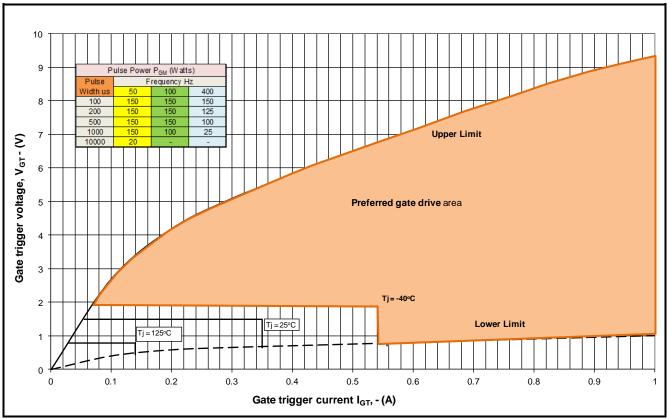


Fig14 Gate Characteristics

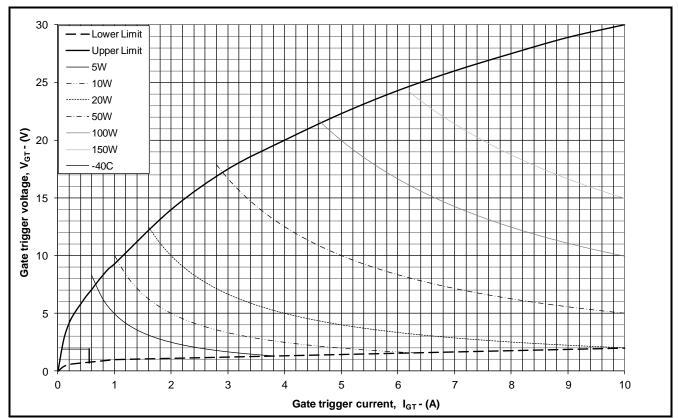


Fig. 15 Gate characteristics





PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

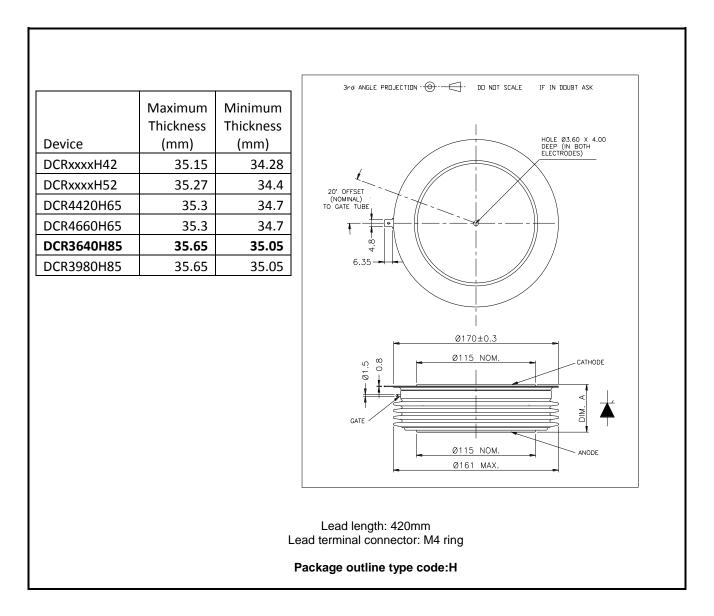


Fig.16 Package outline





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